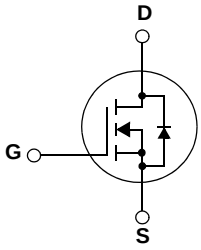
KERSEMI ELECTRONIC CO.,LTD.

KSM22N50N

N-Channel MOSFET
500V, 22A, 0.22Ω

TO-220



Features

- $R_{DS(on)}$ = 0.185Ω (Typ.)@ V_{GS} = 10V, I_D = 11A
- Low gate charge (Typ. 49nC)
- Low C_{rss} (Typ. 24pF)
- Fast switching
- 100% avalanche tested
- Improve dv/dt capability
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Kersemi proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switching mode power supplies and active power factor correction.

MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		KSM22N50N	Units
V_{DSS}	Drain to Source Voltage		500	V
V_{GSS}	Gate to Source Voltage		±30	V
I_D	Drain Current	-Continuous (T_C = 25°C)	22	A
		-Continuous (T_C = 100°C)	13.2	
I_{DM}	Drain Current	- Pulsed (Note 1)	88	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		1000	mJ
I_{AR}	Avalanche Current (Note 1)		22	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		31.25	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		10	V/ns
P_D	Power Dissipation	(T_C = 25°C)	312.5	W
		- Derate above 25°C	2.5	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	KSM22N50N	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
KSM22N50N	KSM22N50N	TO-220	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V,	500	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.45	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 500V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 400V, T_C = 125°C	-	-	10	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 11A	-	0.185	0.22	Ω
g_{FS}	Forward Transconductance	V_{DS} = 20V, I_D = 11A	-	24.4	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V f = 1MHz	-	2456	3200	pF
C_{oss}	Output Capacitance		-	351	460	pF
C_{rss}	Reverse Transfer Capacitance		-	24	50	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 400V, I_D = 22A V_{GS} = 10V (Note 4)	-	49	65	nC
Q_{gs}	Gate to Source Gate Charge		-	15	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	19	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 250V, I_D = 22A R_G = 4.7Ω (Note 4)	-	22	55	ns
t_r	Turn-On Rise Time		-	50	110	ns
$t_{d(off)}$	Turn-Off Delay Time		-	48	110	ns
t_f	Turn-Off Fall Time		-	35	80	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	22	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	88	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 22A	-	-	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 22A dI_F/dt = 100A/μs	-	472	-	ns
Q_{rr}	Reverse Recovery Charge		-	6.5	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 4.1mH, I_{AS} = 22A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 22A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

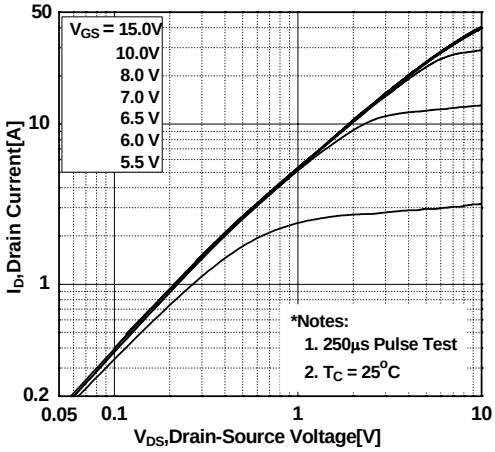


Figure 2. Transfer Characteristics

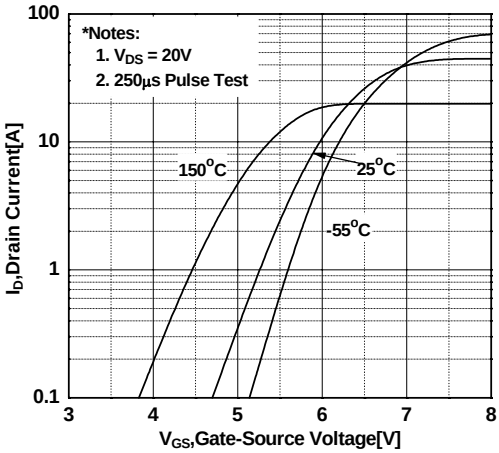


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

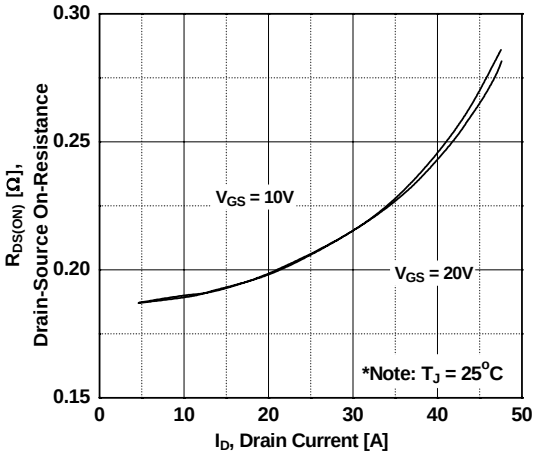


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

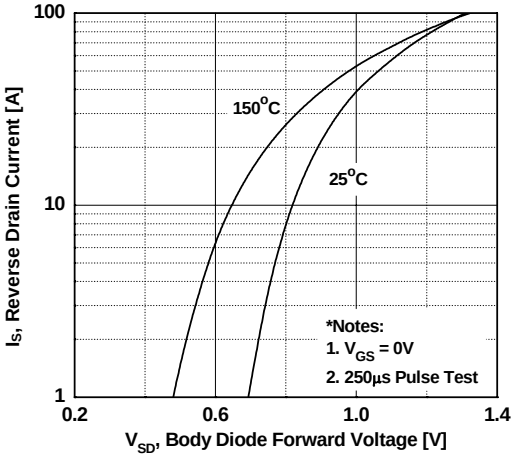


Figure 5. Capacitance Characteristics

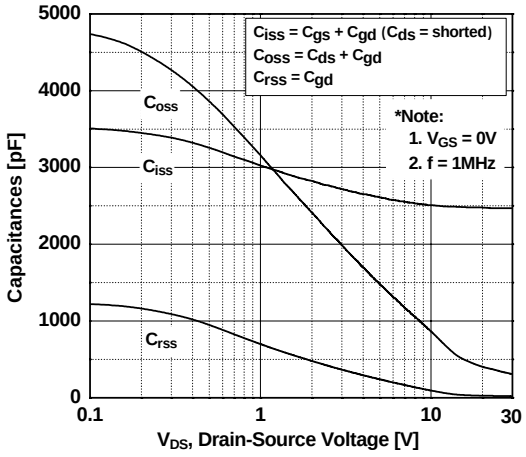
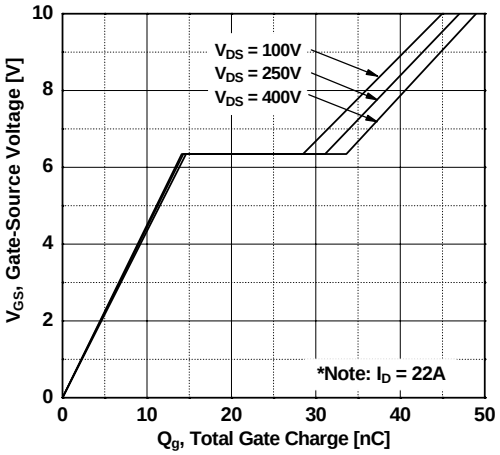


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

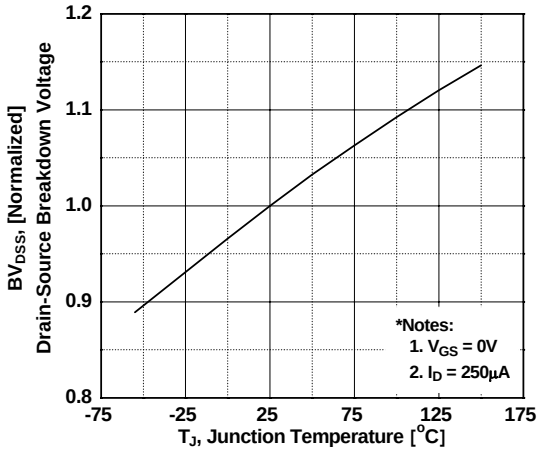


Figure 8. On-Resistance Variation vs. Temperature

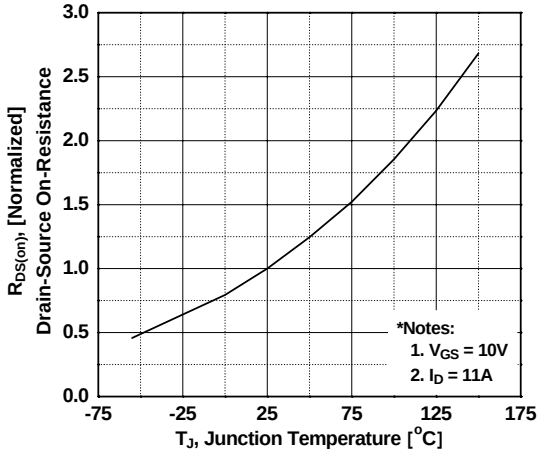


Figure 9. Maximum Safe Operating Area - FDP22N50N

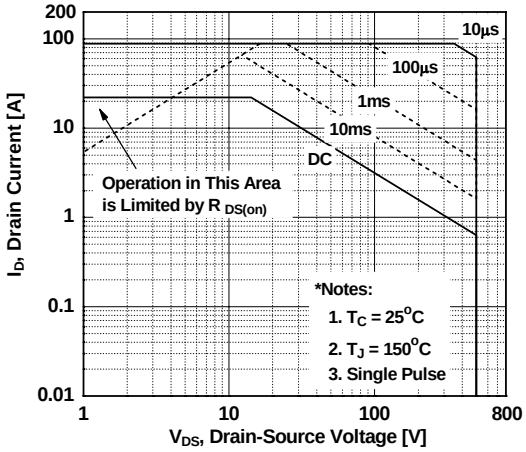


Figure 10. Maximum Drain Current vs. Case Temperature

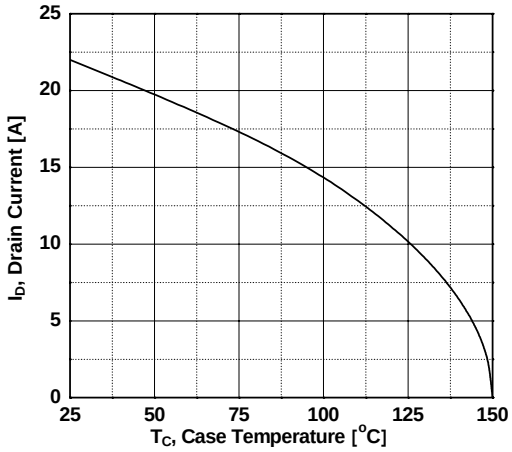
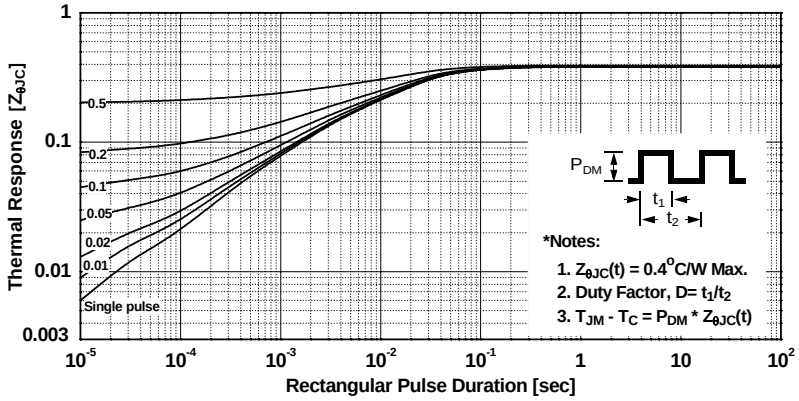
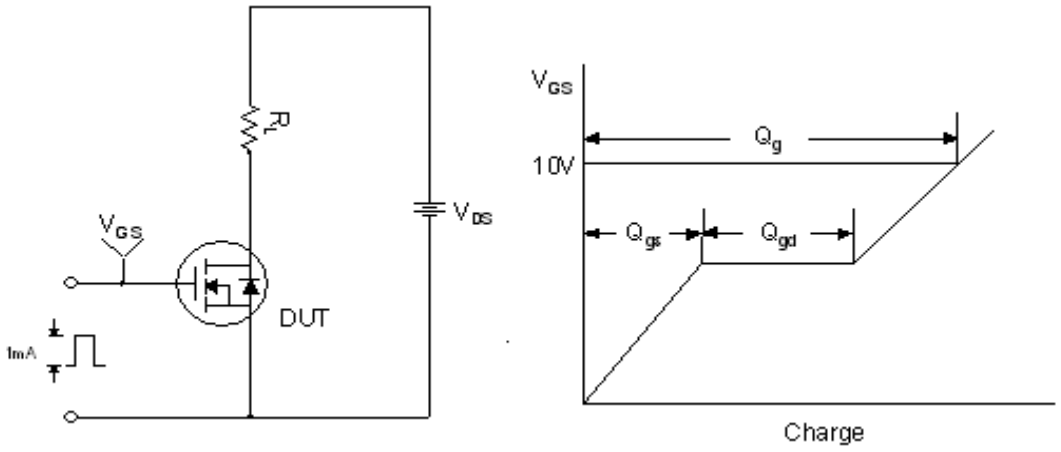


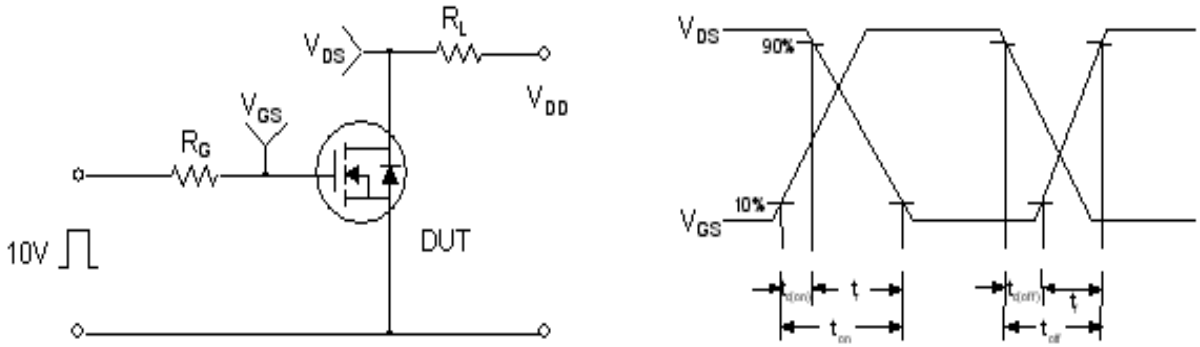
Figure 10. Transient Thermal Response Curve - FDP22N50N



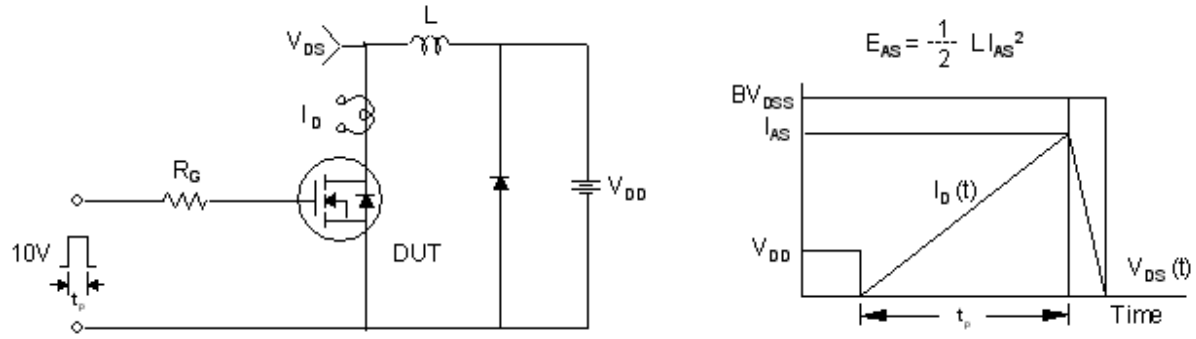
Gate Charge Test Circuit & Waveform



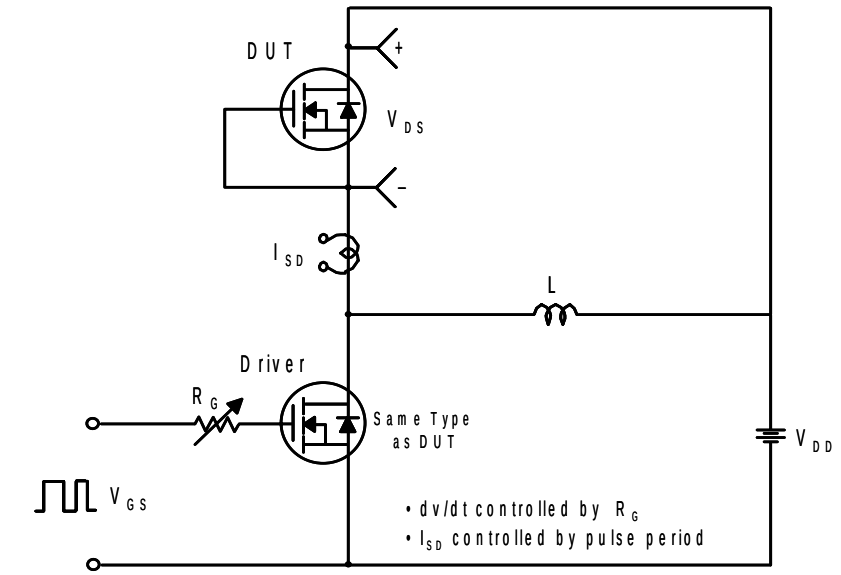
Resistive Switching Test Circuit & Waveforms

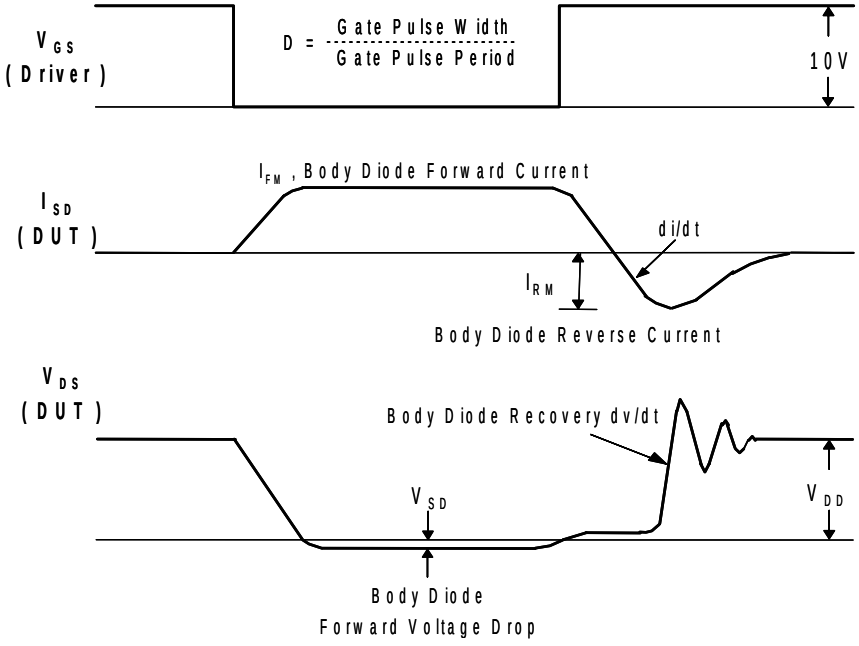


Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-220